



**Composition for the chemical-mechanical polishing of metal and metal/-
dielectric structures with high selectivity**

A b s t r a c t

A composition for the chemical-mechanical polishing of metal and metal/dielectric structures, containing 7 to 100% by volume of a cationically stabilized silica sol which contains 30% by weight of SiO₂ and the SiO₂ particles of which have a mean particle size of less than 300 nm, with a pH of from 4 to 10, is distinguished by a TaN removal rate of ≥ 40 nm per min and an improved barrier layer:metal selectivity of at least 2:1 or greater and a barrier layer:dielectric selectivity of at least 2:1 or above.

